

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)



ON Semiconductor®

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## Darlington Complementary Silicon Power Transistors

These devices are designed for general purpose and low speed switching applications.

### Features

- High DC Current Gain –  $h_{FE} = 2500$  (typ.) at  $I_C = 4.0$
- Collector–Emitter Sustaining Voltage at 100 mAdc  
 $V_{CEO(sus)} = 80$  Vdc (min) – BDX33B, BDX334B  
 $= 100$  Vdc (min) – BDX33C, BDX334C
- Low Collector–Emitter Saturation Voltage  
 $V_{CE(sat)} = 2.5$  Vdc (max) at  $I_C = 3.0$  Adc  
– BDX33B, 33C/34B, 34C
- Monolithic Construction with Build–In Base–Emitter Shunt Resistors
- These Devices are Pb–Free and are RoHS Compliant\*

### MAXIMUM RATINGS

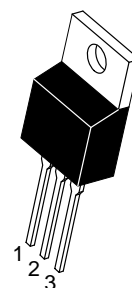
Rating	Symbol	Value	Unit
Collector–Emitter Voltage BDX33B, BDX34B BDX33C, BDX34C	$V_{CEO}$	80 100	Vdc
Collector–Base Voltage BDX33B, BDX34B BDX33C, BDX34C	$V_{CB}$	80 100	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current Continuous Peak	$I_C$	10 15	Adc
Base Current	$I_B$	0.25	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	70 0.56	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

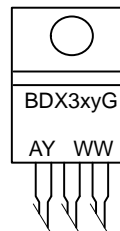
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.78	$^\circ\text{C}/\text{W}$

## DARLINGTON 10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 80–100 VOLTS, 65 WATTS



TO-220  
CASE 221A  
STYLE 1

### MARKING DIAGRAM



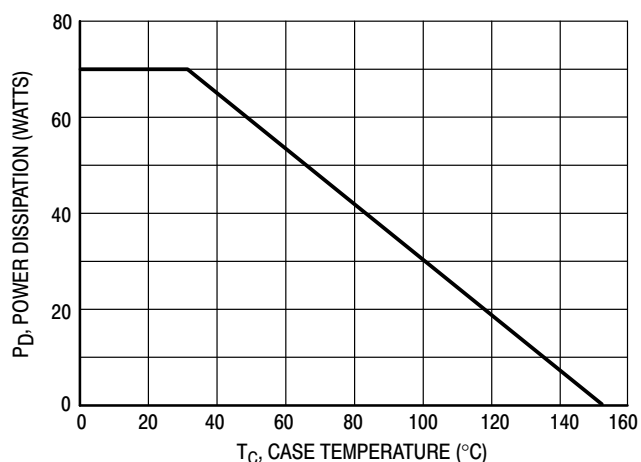
BDX3xy = Device Code  
x = 3 or 4  
y = B or C  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb–Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)



**Figure 1. Power Derating**

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	BDX33B/BDX34B BDX33C/BDX34C	V <sub>CEO(sus)</sub>	80 100	– –	Vdc
Collector–Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0, R <sub>BE</sub> = 100)	BDX33B/BDX34B BDX33C/BDX33C	V <sub>CER(sus)</sub>	80 100	– –	Vdc
Collector–Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0, V <sub>BE</sub> = 1.5 Vdc)	BDX33B/BDX34B BDX33C/BDX34C	V <sub>CEX(sus)</sub>	80 100	– –	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 1/2 rated V <sub>CEO</sub> , I <sub>B</sub> = 0)	T <sub>C</sub> = 25°C T <sub>C</sub> = 100°C	I <sub>CEO</sub>	– –	0.5 10	mAdc
Collector Cutoff Current (V <sub>CB</sub> = rated V <sub>CBO</sub> , I <sub>E</sub> = 0)	T <sub>C</sub> = 25°C T <sub>C</sub> = 100°C	I <sub>CBO</sub>	– –	1.0 5.0	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	–	10	mAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 1) (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 3.0 Vdc)	BDX33B, 33C/34B, 34C	h <sub>FE</sub>	750	–	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 6.0 mAdc)	BDX33B, 33C/34B, 34C	V <sub>CE(sat)</sub>	–	2.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 3.0 Vdc)	BDX33B, 33C/34B, 34C	V <sub>BE(on)</sub>	–	2.5	Vdc
Diode Forward Voltage (I <sub>C</sub> = 8.0 Adc)		V <sub>F</sub>	–	4.0	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. Pulse Test non repetitive: Pulse Width = 0.25 seconds.

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

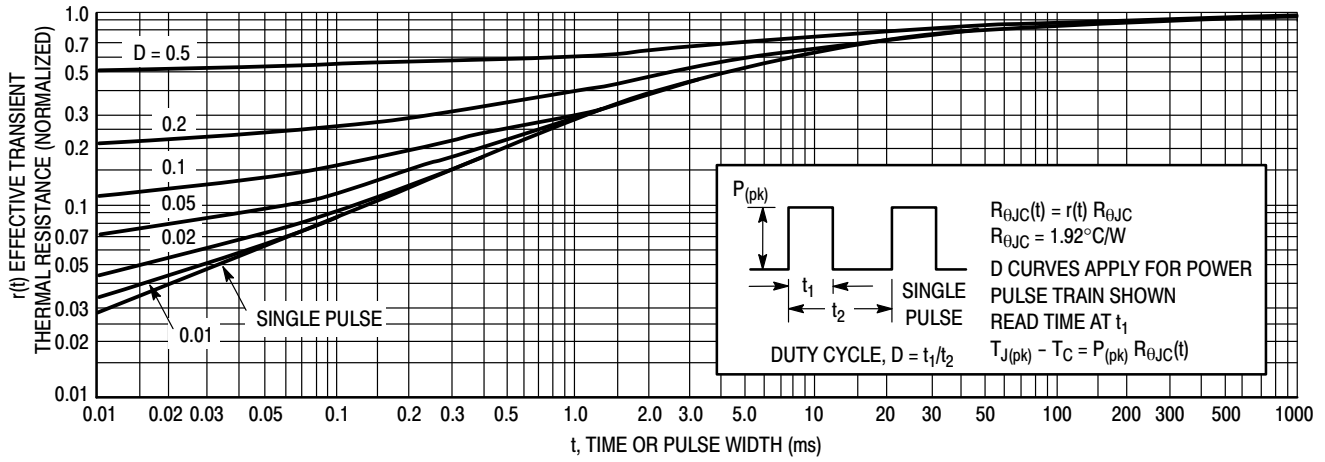


Figure 1. Thermal Response

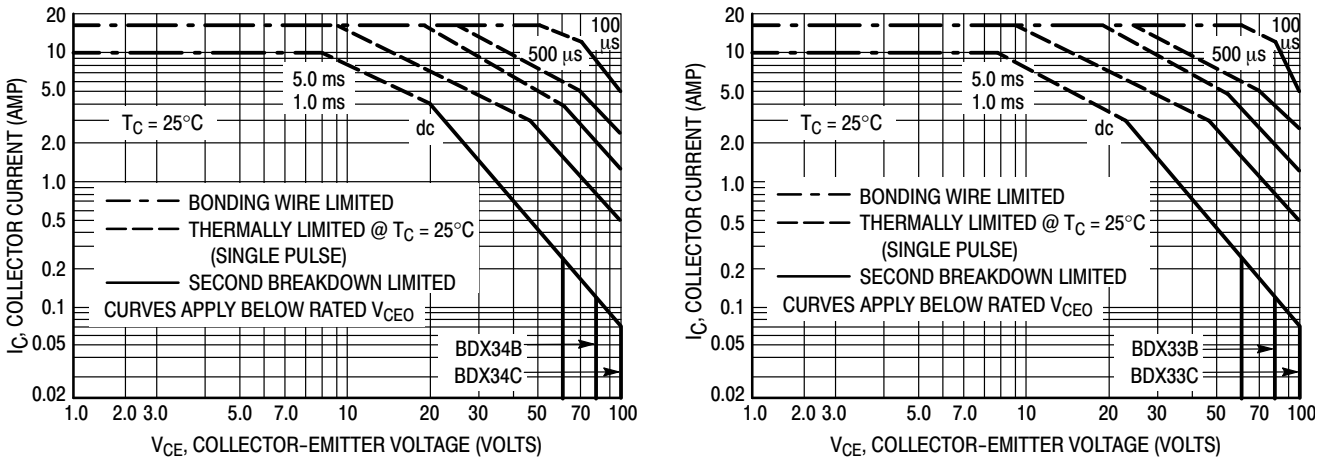


Figure 2. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 3 is based on  $T_{J(pk)}$

=  $150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} = 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

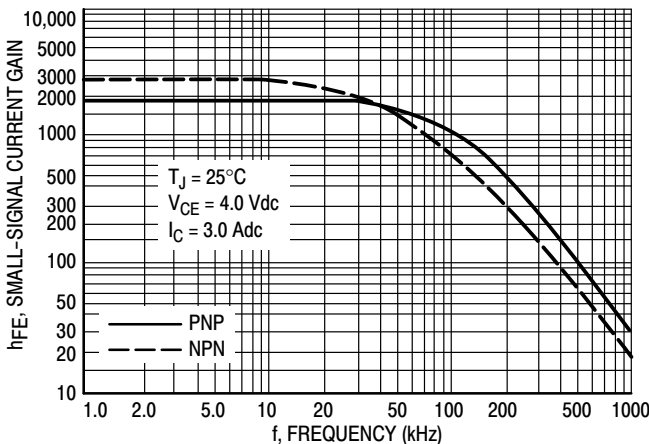


Figure 3. Small-Signal Current Gain

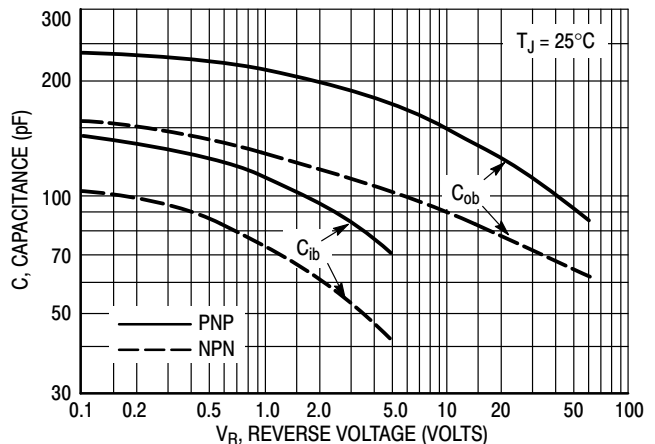
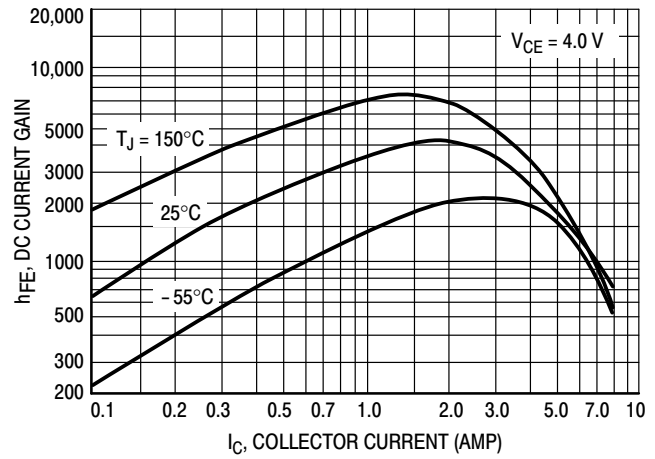
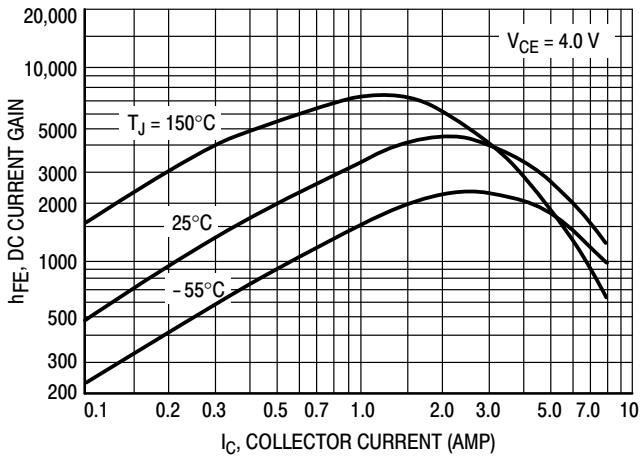


Figure 4. Capacitance

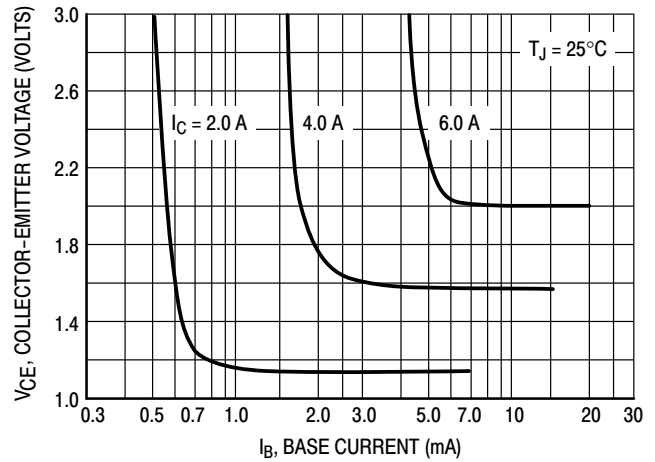
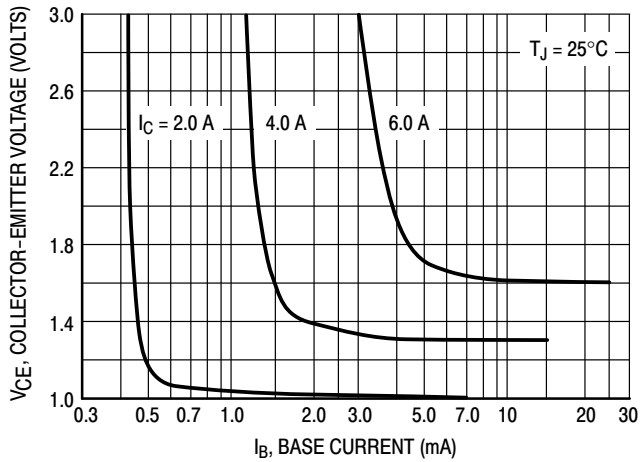
# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

**NPN**  
**BDX33B, 33C**

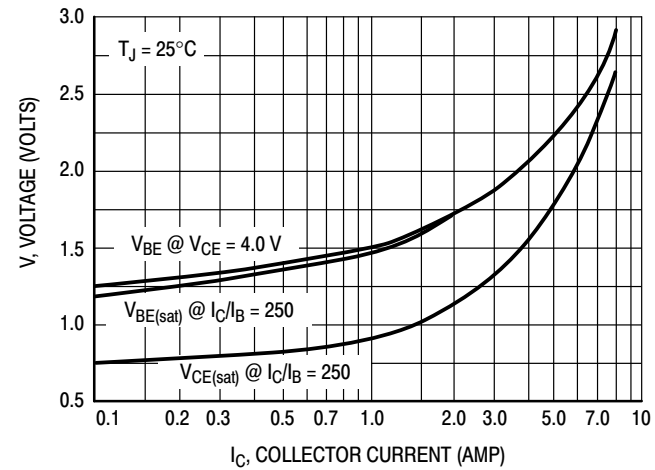
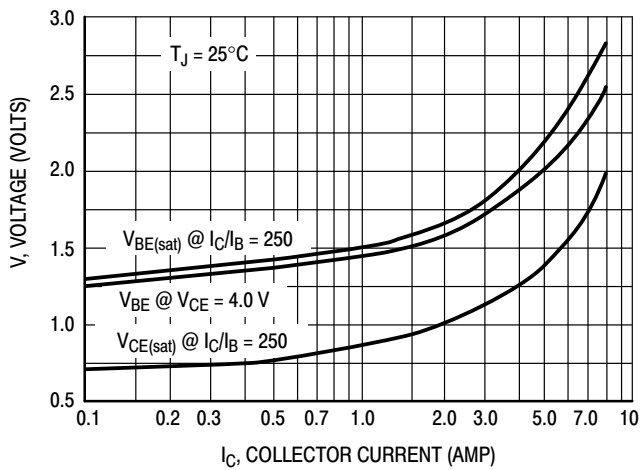
**PNP**  
**BDX34B, 34C**



**Figure 5. DC Current Gain**



**Figure 6. Collector Saturation Region**



**Figure 7. "On" Voltages**

## BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

### ORDERING INFORMATION

Device	Package	Shipping†
BDX33BG	TO-220 (Pb-Free)	50 Units / Rail
BDX33CG	TO-220 (Pb-Free)	50 Units / Rail
BDX34BG	TO-220 (Pb-Free)	50 Units / Rail
BDX34CG	TO-220 (Pb-Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.